

## IN THE SPECIFICATION

Please amend the Abstract as follows:

--This invention provides ~~is to provide~~ a semiconductor laser device and method of manufacture with a small interval between light emitting points of laser lights ~~and a method of manufacturing the same~~. A first light emitting element [[1a]] having a semiconductor substrate [[12a]] and a laser oscillation section [[10a]], and a second light emitting element [[2a]] having a laser oscillation section [[4a]], are brought together with a ridged waveguide [[8]] of the laser oscillation section [[10a]] facing the ridged waveguide [[5]] of the laser oscillation section [[4a]], and then bonded together by virtue of SOGs [[3a]] having a small thickness. A conductive wiring layer [[Qa1]] electrically connected with an ohmic electrode layer [[9a]] on the ridged waveguide [[8a]], and a wiring layer [[Qa2]] electrically connected with an ohmic electrode layer [[6a]] on the ridged waveguide [[5a]], are arranged to extend until the insulating layer [[11a]] on the semiconductor substrate [[12a]]. Further, the ohmic electrodes [[Pa1]] and [[Pa2]] are formed on the bottom surface of the semiconductor substrate [[12a]] and the top surface of the laser oscillation section [[4a]], respectively. ~~In this way, when a drive current is supplied between the ohmic electrode Pa1 and the wiring layer Qa1, the laser oscillation section 10a will emit a light. On the other hand, when a drive current is supplied between the ohmic electrode Pa2 and the wiring layer Qa2, the laser oscillation section 4a will emit a light. In this manner, since the laser oscillation sections 4a and 10a are bonded together by virtue of SOGs 3a having a small thickness, it is allowed to form a semiconductor laser device with a small interval between light emitting points.--~~